



Description

The 3020K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

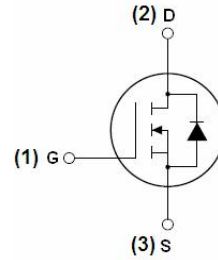
- $V_{DS} = 30V, I_D = 20A$
 $R_{DS(ON)} < 13m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 24m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low $R_{ds(on)}$
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

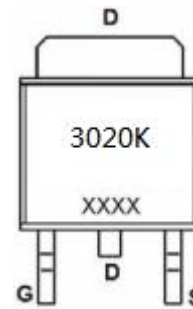
- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

100% UIS TESTED!

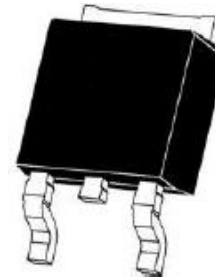
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin Assignment



TO-252-2L top view

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	20	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	14.5	A
Pulsed Drain Current	I_{DM}	80	A
Maximum Power Dissipation	P_D	24	W
Derating factor		0.27	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	72	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$



富满微电子集团股份有限公司

FINE MADE ELECTRONICS GROUP CO., LTD.

3020K (文件编号: S&CIC1876)

N-Channel Trench Power MOSFET

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3.8	°C/W
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Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

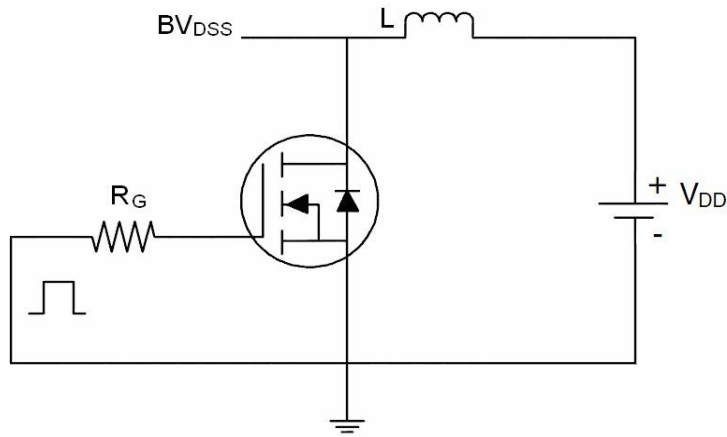
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=10A$	-	10	13	m Ω
		$V_{GS}=4.5V, I_D=5A$	-	17	24	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=10A$	22	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	956	-	PF
Output Capacitance	C_{oss}		-	148	-	PF
Reverse Transfer Capacitance	C_{rss}		-	102	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=0.75\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	5.2	-	nS
Turn-on Rise Time	t_r		-	12.6	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20.5	-	nS
Turn-Off Fall Time	t_f		-	6.8	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=10A,$ $V_{GS}=10V$	-	18.5	-	nC
Gate-Source Charge	Q_{gs}		-	3.2	-	nC
Gate-Drain Charge	Q_{gd}		-	4.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=10A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	20	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = 10A$ $di/dt = 100A/\mu\text{s}$ ^(Note 3)	-	21	-	nS
Reverse Recovery Charge	Q_{rr}		-	11	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

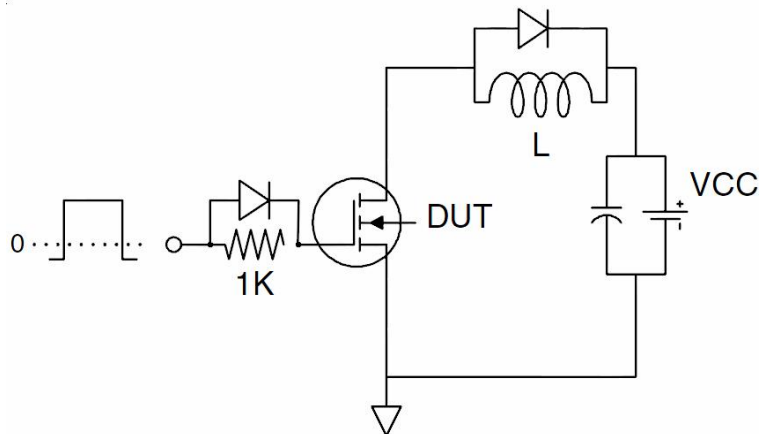
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

Test circuit

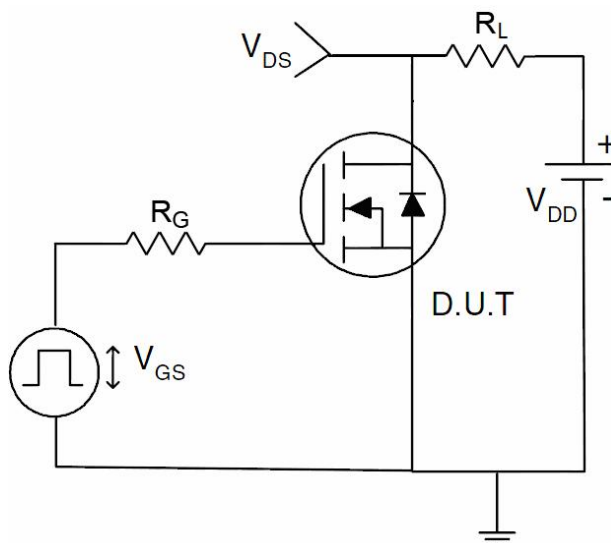
1) EAS test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)

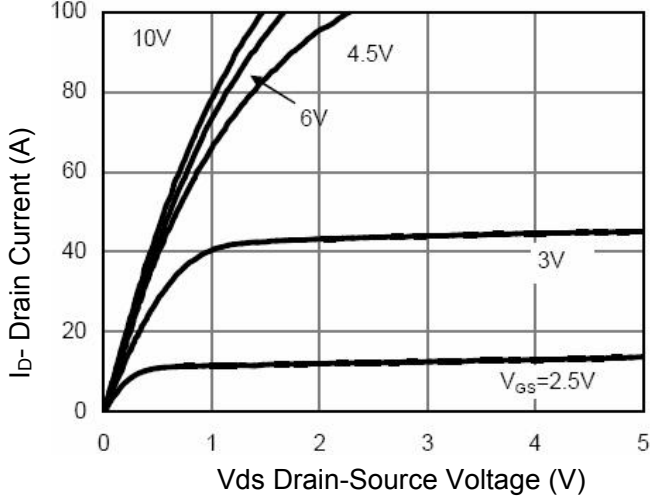


Figure 1 Output Characteristics

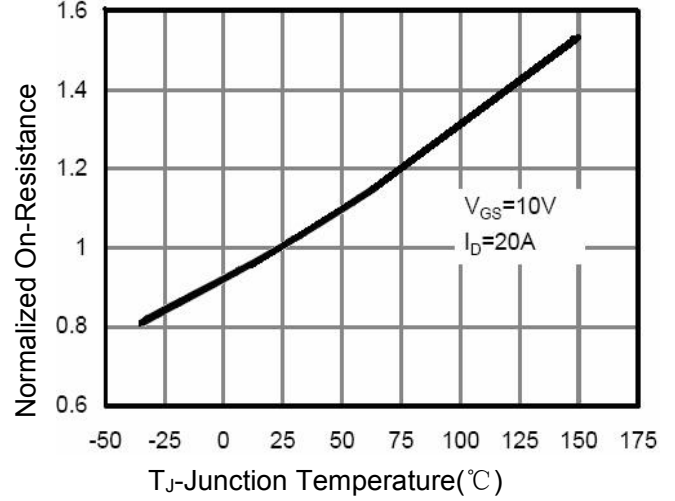


Figure 4 Rdson-Junction Temperature

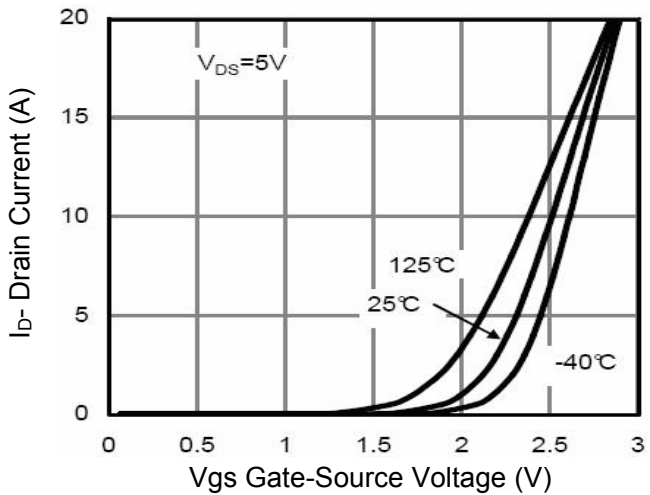


Figure 2 Transfer Characteristics

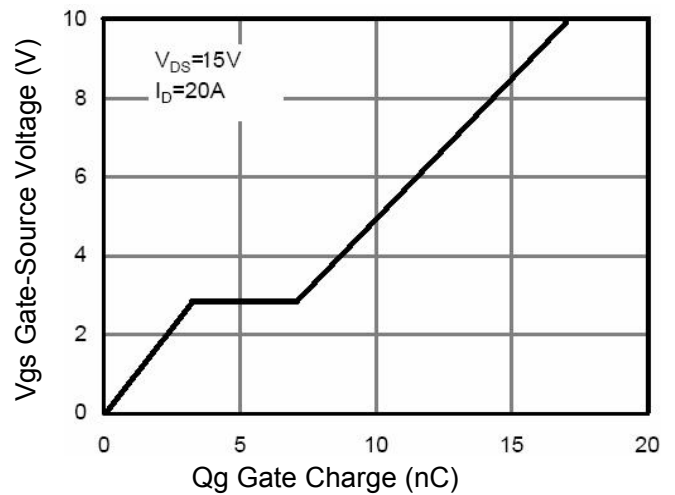


Figure 5 Gate Charge

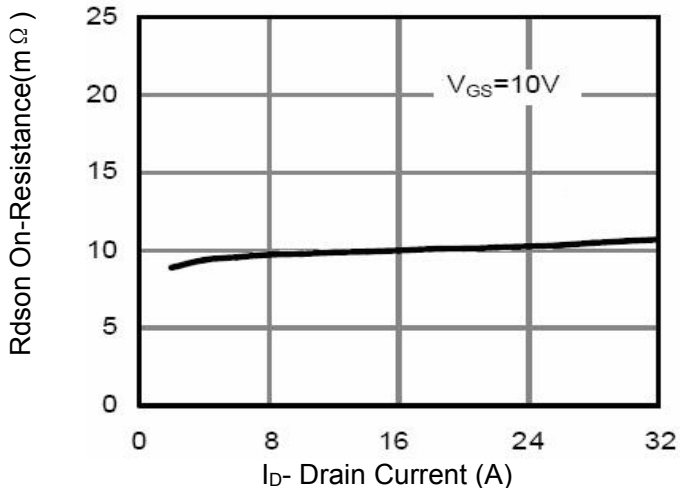


Figure 3 Rdson- Drain Current

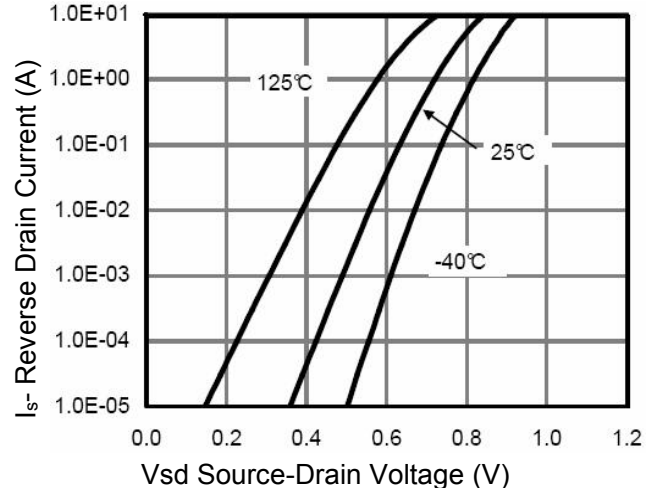


Figure 6 Source- Drain Diode Forward

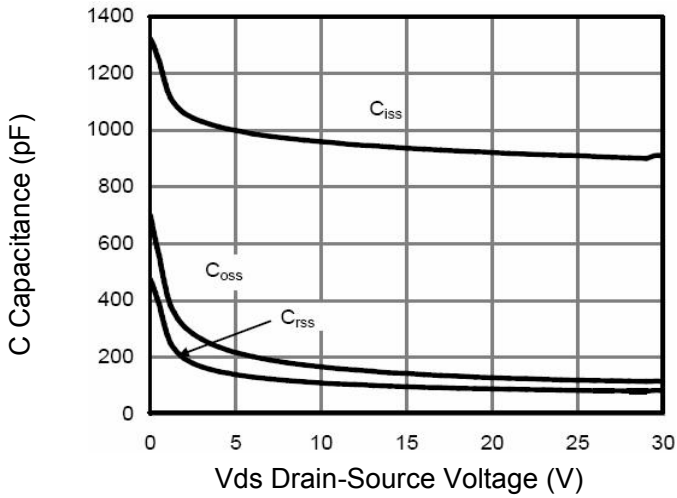


Figure 7 Capacitance vs Vds

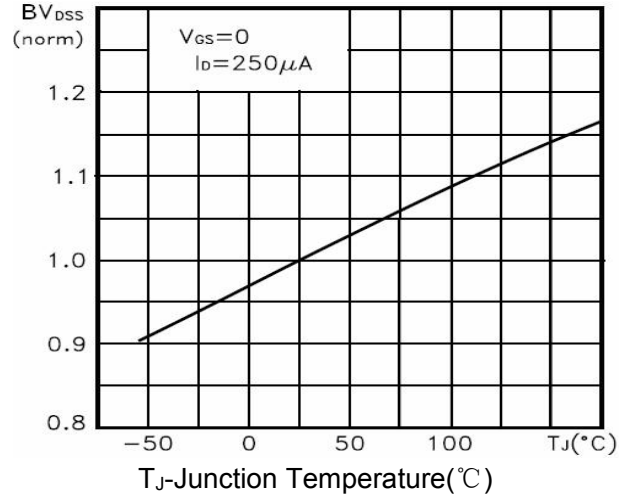


Figure 9 BV_{DSS} vs Junction Temperature

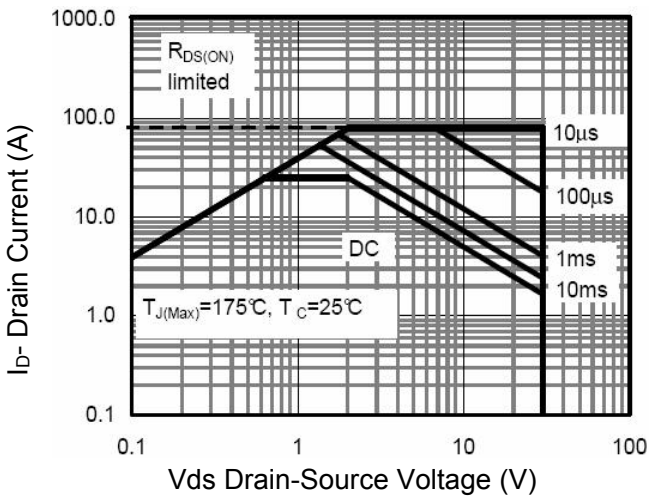


Figure 8 Safe Operation Area

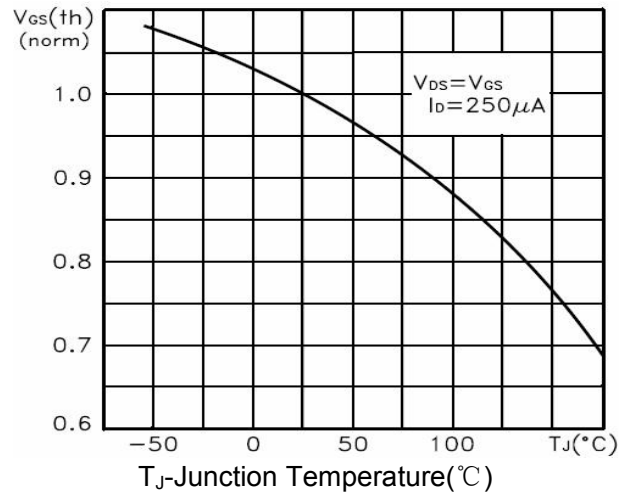


Figure 10 $V_{GS(th)}$ vs Junction Temperature

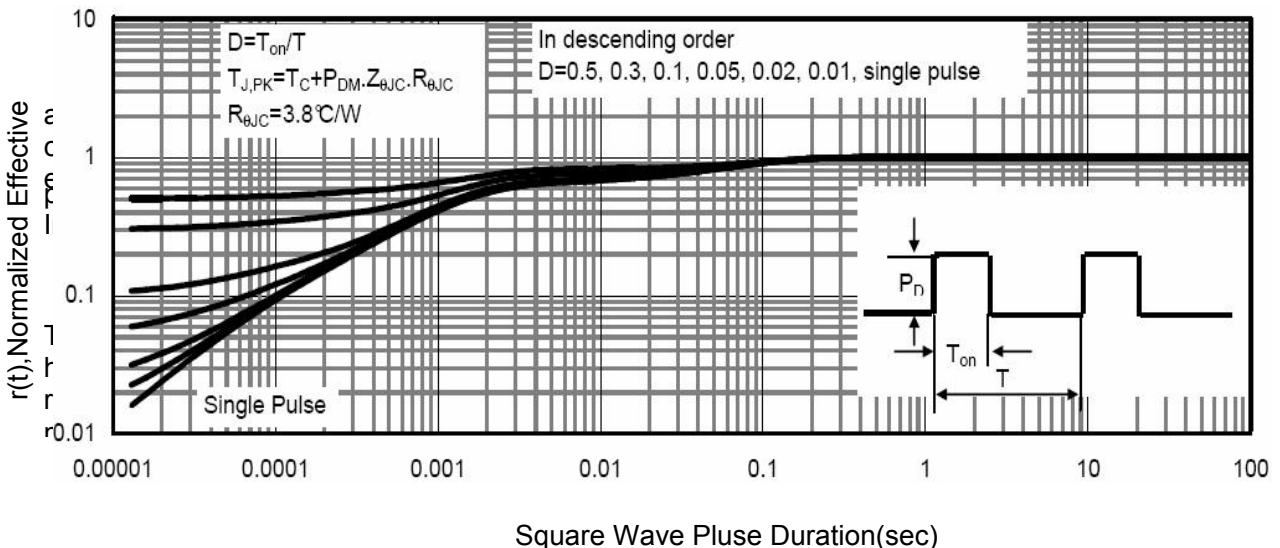
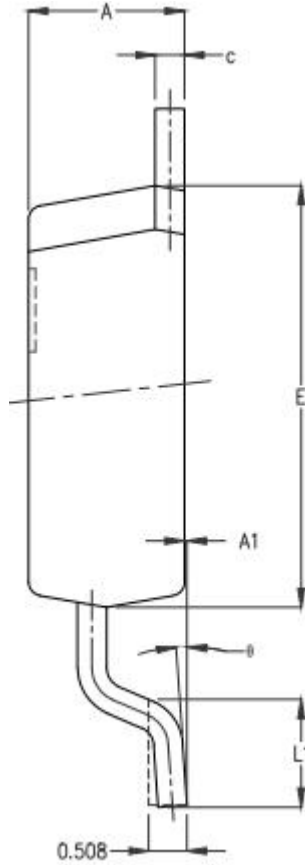
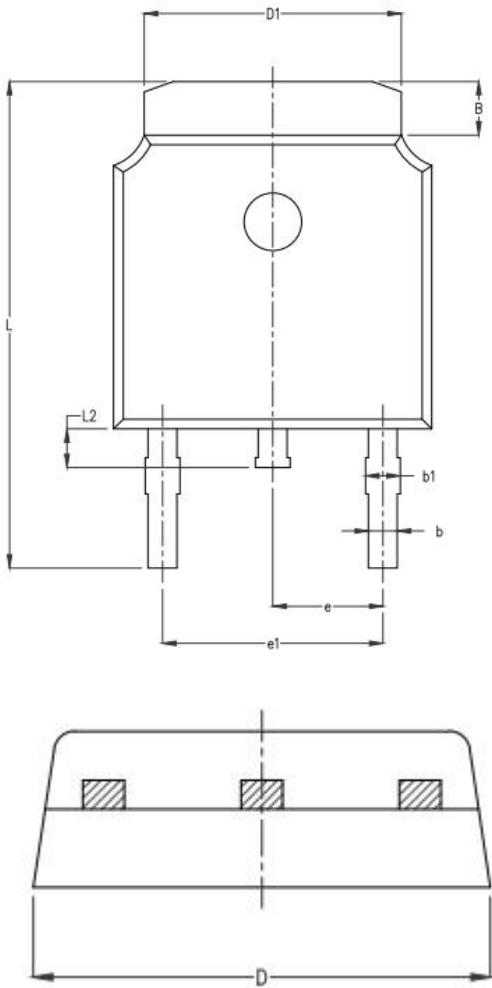


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252 Package Information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.15	2.25	2.35
A1	0.00	0.06	0.12
B	0.96	1.11	1.26
b	0.59	0.69	0.79
b1	0.69	0.81	0.93
c	0.34	0.42	0.50
D	6.45	6.60	6.75
D1	5.23	5.33	5.43
E	5.95	6.10	6.25
e	2.286TYP.		
e1	4.47	4.57	4.67
L	9.90	10.10	10.30
L1	1.40	1.55	1.70
L2	0.60	0.80	1.00
θ	0°	4°	8°